ABSTRACT

Proposed is a Cu-Mn alloy sputtering target, wherein the Mn content is 0.05 to 20wt%, the total amount of Be, B, Mg, Al, Si, Ca, Ba, La, and Ce is 500wtppm or less, and the remainder is Cu and unavoidable impurities. Specifically, provided are a copper alloy wiring for semiconductor application, a sputtering target for forming this wiring, and a manufacturing method of a copper alloy wiring for semiconductor application. The copper alloy wiring itself for semiconductor application is equipped with a self-diffusion suppression function for effectively preventing the contamination around the wiring caused by the diffusion of active Cu, improving electromigration (EM) resistance, corrosion resistance and the like, enabling and facilitating the arbitrary formation of a barrier layer, and simplifying the deposition process of the copper alloy wiring for semiconductor application.